



# YJD27G10A

---

## N-Channel Enhancement Mode Field Effect Transistor

### Product Summary

|                                   |      |
|-----------------------------------|------|
| $V_{DS}$                          | 100V |
| $I_D$                             | 27A  |
| $R_{DS(ON)}$ ( at $V_{GS}=10V$ )  | 29m  |
| $R_{DS(ON)}$ ( at $V_{GS}=4.5V$ ) | 47m  |
| 100% EAS Tested                   |      |
| 100% $V_{DS}$ Tested              |      |



**YJD27G10A**



# YJD27G10A

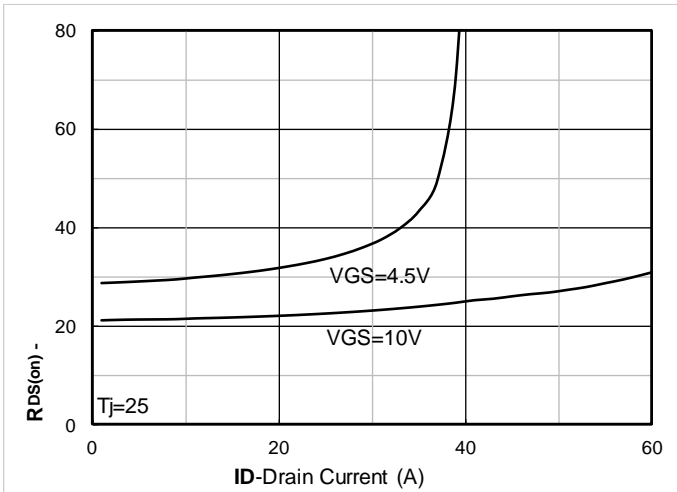


Figure 7. RDS(on) VS Drain Current

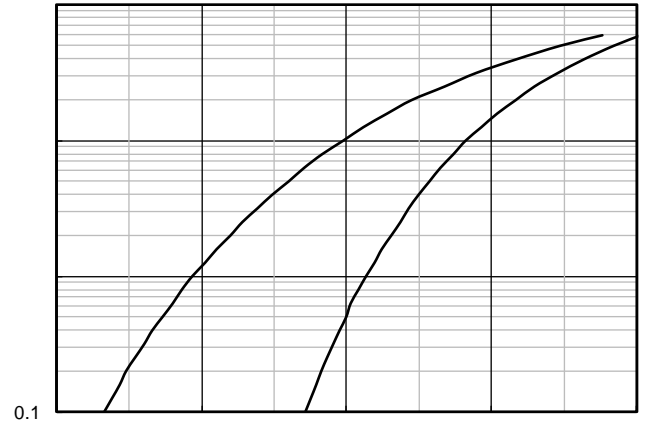


Figure 8. Forward characteristics of reverse diode

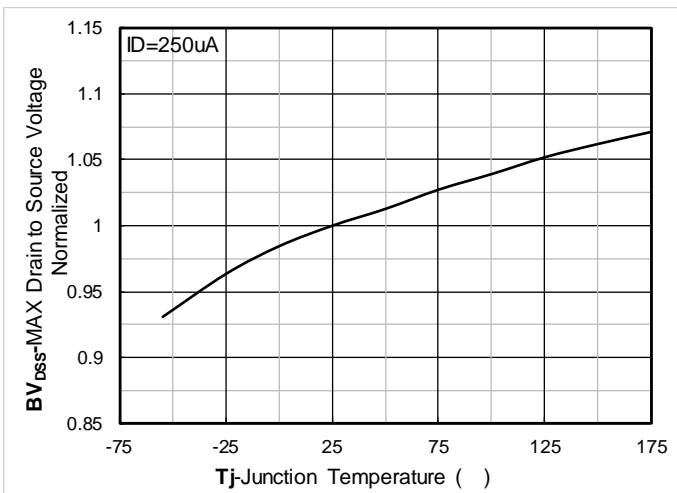


Figure 9. Normalized breakdown voltage

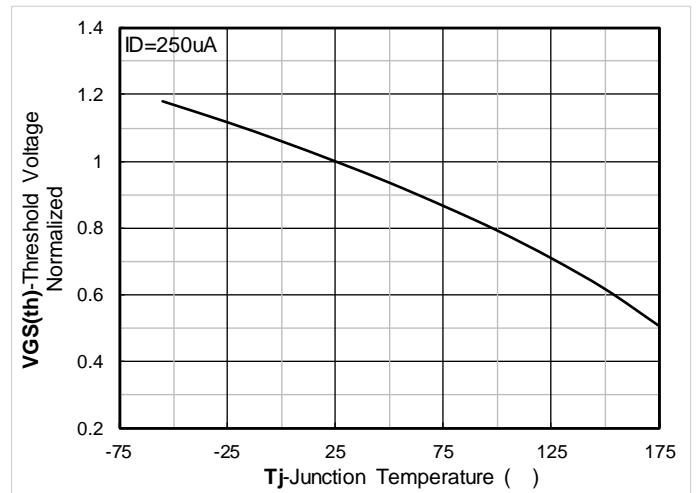


Figure 10. Normalized threshold voltage





# YJD27G10A



Figure B. Gate Charge Test Circuit & Waveform



Figure C. Resistive Switching Test Circuit & Waveform

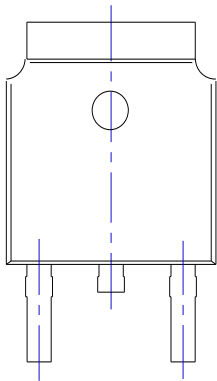


Figure D. Diode Recovery Test Circuit & Waveform



# YJD27G10A

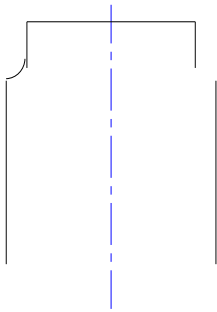
## TO-252-B Package information



TOP VIEW



SIDE VIEW



BOTTOM VIEW

SUGGESTED SOLDER PAD LAYOUT

| SYMBOL | DIMENSIONS |       |  |  |  |
|--------|------------|-------|--|--|--|
|        | INCHES     |       |  |  |  |
|        | MIN.       | NOM.  |  |  |  |
| A1     | 0.000      |       |  |  |  |
| A2     | 0.087      | 0.091 |  |  |  |
| A3     | 0.035      | 0.039 |  |  |  |
| b      | 0.026      | 0.030 |  |  |  |
| c      | 0.018      | 0.020 |  |  |  |
| D      | 0.256      | 0.260 |  |  |  |
| D1     |            |       |  |  |  |
| D2     | 0.181      | 0.189 |  |  |  |
| E      | 0.390      | 0.398 |  |  |  |
| E1     | 0.236      | 0.240 |  |  |  |

**NOTE:**

- 1. PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
- 2. TOLERANCE 0.1mm UNLESS OTHERWISE SPECIFIED.
- 3. THE PAD LAYOUT IS FOR REFERENCE PURPOSES ONLY.

**YJD27G10A**